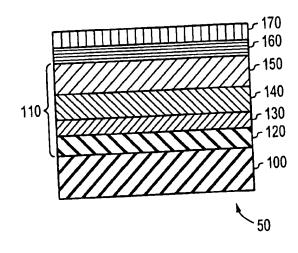
Title: Semiconductor Heterostructures and Related Methods
Inventor(s): Leitz et al.
Atty Docket No. ASC-058A
Filing Date: August 22, 2003
Atty/Agent: MLBeloborodov/BRChase
Formal Drawings

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FIG. 1

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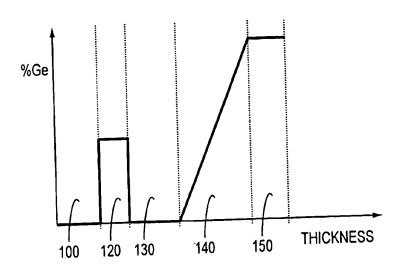


FIG. 2

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QUALITATIVE EVALUATION OF DISLOCATION PILE-UP DENSITY			
H* = 0.6 T <sub>crit</sub>	H = 1.25 T <sub>crit</sub>	H = 2 T <sub>crit</sub>	H = 5 T <sub>crit</sub>
HIGH	MEDIUM	LOW	LOW
HIGH	MEDIUM	MEDIUM	LOW
HIGH	MEDIUM	MEDIUM	LOW
	H* = 0.6 T <sub>crit</sub> HIGH HIGH	H* = 0.6 T <sub>crit</sub> H = 1.25 T <sub>crit</sub> HIGH MEDIUM  HIGH MEDIUM	HIGH MEDIUM LOW  HIGH MEDIUM MEDIUM  HIGH MEDIUM MEDIUM  HIGH MEDIUM MEDIUM

<sup>\*</sup> THICKNESS (H) OF THE SEED LAYER RELATIVE TO ITS CRITICAL THICKNESS (T<sub>crit</sub>).

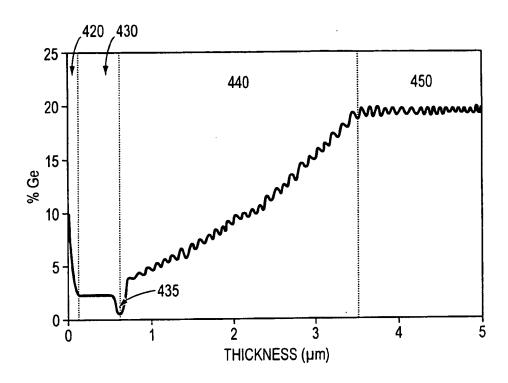
FIG. 3

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FIG. 4

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Formal Drawings

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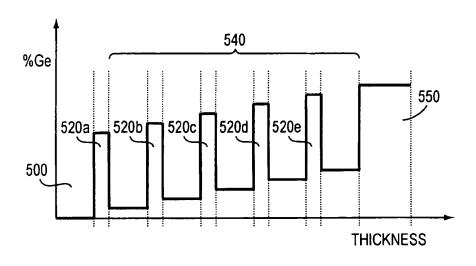


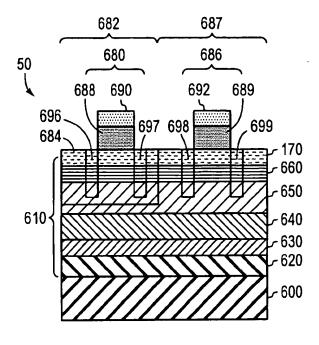
FIG. 5

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Methods

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Formal Drawings

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FIG. 6